

No.1397

2SC3482

NPN Triple Diffused Planar Type Silicon Transistor
 FOR HIGH DEFINITION CRT DISPLAY HORIZONTAL
 DEFLECTION OUTPUT APPLICATIONS
 (BUILT-IN DAMPER DIODE)


**Features:**

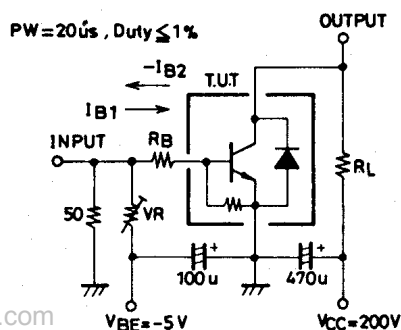
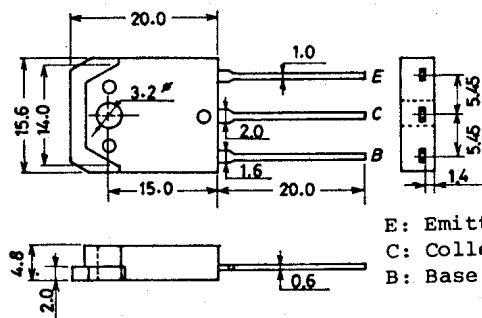
- High breakdown voltage and high reliability
- High switching speed: $t_f=0.3\mu s$ max.
- Capable of being mounted easily due to one-point fixing type plastic mold package

Absolute Maximum Ratings at $T_a=25^\circ C$

| | | | unit |
|------------------------------|------|-------------|-------|
| Collector to Base Voltage | VCBO | 1500 | V |
| Collector to Emitter Voltage | VCEO | 800 | V |
| Emitter to Base Voltage | VEBO | 7 | V |
| Collector Current | IC | 6 | A |
| Peak Collector Current | icp | 16 | A |
| Collector Dissipation | PC | Tc=25°C | 120 W |
| Junction Temperature | Tj | 150 | °C |
| Storage Temperature | Tstg | -55 to +150 | °C |

Electrical Characteristics at $T_a=25^\circ C$

| | | | min | typ | max | unit |
|--------------------------|----------|--|------|-----|-----|------|
| Collector Cutoff Current | ICBO | ICB=800V, IE=0 | | | 10 | uA |
| Emitter Cutoff Current | IEBO | VEB=4V, IC=0 | 40 | | 130 | mA |
| DC Current Gain | hFE | VCE=5V, IC=1A | 8 | | | |
| Gain Bandwidth Product | fT | VCE=10V, IC=1A | | 3 | | MHz |
| C-E Saturation Voltage | VCE(sat) | IC=5A, IB=1.2A | | | 5 | V |
| B-E Saturation Voltage | VBE(sat) | IC=5A, IB=1.2A | | | 1.5 | V |
| C-B Breakdown Voltage | V(BR)CBO | IC=5mA, IE=0 | 1500 | | | V |
| C-E Breakdown Voltage | V(BR)CEO | IC=5mA, RBE=∞ | 800 | | | V |
| E-B Breakdown Voltage | V(BR)EBO | IE=200mA, IC=0 | 7 | | | V |
| Diode Forward Voltage | VF | IEC=6A | | | 2 | V |
| Storage Time | tstg | [IC=5A, IB1=1A, IB2=-2A, VCC=200V, RL=40ohm] | | | 3.0 | us |
| Fall Time | tf | | | | 0.3 | us |

Switching Time Test Circuit**Case Outline 2022
(unit:mm)**

E: Emitter
 C: Collector
 B: Base

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